External Project Report on Digital Logic Design (EET1211)

TOPIC:
DESIGN AND IMPLEMENT A 2-BIT AND 4-BIT MAGNITUDE COMPARATOR USING LOGIC GATES

Submitted by

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Declaration

We, the undersigned students of B. Tech. of "**Computer Science and Engineering"**Department hereby declare that we own the full responsibility for the information, results etc. provided in this PROJECT titled **"Design and implement a 2-bit and a 4-bit Magnitude Comparator using logic gates".** submitted to **Siksha 'O' Anusandhan Deemed to be University, Bhubaneswar** for the partial fulfillment of the subject **Digital Logic Design (EET 1211)**. We have taken care in all respect to honor the intellectual property right and have acknowledged the contribution of others for using them in academic purpose and further declare that in case of any violation of intellectual property right or copyright we, as the candidate(s), will be fully responsible for the same.

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ABSTRACT:

A 2-bit magnitude comparator circuit compares two 2-bit binary numbers to determine their relative magnitudes. It typically consists of XOR gates, AND gates, and OR gates to compare corresponding bits. The output signals indicate whether the numbers are equal, one is greater, or the other is greater.

Similarly, a 4-bit magnitude comparator circuit compares two 4-bit binary numbers. It extends the principles of the 2-bit comparator, using XOR, AND, and OR gates for each pair of corresponding bits. The output signals provide information about the relationship between the two 4-bit numbers in terms of equality and magnitude.

In both cases, the comparator circuits are designed to efficiently analyze binary numbers and produce relevant output based on the relative magnitudes of the compared values.

Contents

1. Introduction

“The aim of this project is to design and implement a 2 bit and 4 bit magnitude comparator.”

2-bit magnitude comparator:

A 2-bit magnitude comparator is a digital circuit designed to compare the magnitudes of two 2-bit binary numbers. Its primary function is to determine whether one binary number is greater than, equal to, or less than the other.

The 2-bit magnitude comparator performs a bitwise comparison starting from the most significant bit (MSB) to the least significant bit (LSB).

The comparison is done using logic gates, and the output lines are activated based on the comparison results.

The output lines typically include signals like "A > B," "A < B," and "A = B," indicating the relative magnitudes of the two input numbers.

4-bit magnitude comparator:

A 4-bit magnitude comparator is a digital circuit designed to compare the magnitudes of two 4-bit binary numbers. Similar to its 2-bit counterpart, it determines whether one 4-bit binary number is greater than, equal to, or less than another.

The 4-bit magnitude comparator performs a bitwise comparison starting from the most significant bit (MSB) to the least significant bit (LSB).

The comparison is carried out using logic gates, and the output lines are activated based on the comparison results.

Output lines typically include signals like "A > B," "A < B," and "A = B," indicating the relative magnitudes of the two input numbers.

2. PROBLEM STATEMENT

I. Explanation of problem and identification of input and output variables.
II. Highlighting the constraints.

EXPLAINATION:

In this problem we are going to take 2 numbers for both the sub problems (2 bit and 4 bit).For 2 bit we will have 2 bits for each of the numbers A and B and for 4 bit we will have 4 bits for each of the numbers A and B. The bits of A will be compared to that of B's bit and thereby give us with three outputs where GT will result to 1 if A>B, LT will result to 1 if A<B and ET will result to 1 if a=b.

For 2 BIT:

Input: for the no A 2 bits are: A1, A0
for the no B 2 bits are: B1,B0

Output: There would be comparisons between the no.s A and B creating outputs as
GT (greater than)
LT (less than)
ET (equal to)

For 4 BIT:

Input: for the no A 4 bits are :A3,A2,A1,A0
for the no B 4 bits are:B3,B2,B1,B0

Output: There would be comparisons between the no.s A and B creating outputs as
GT (greater than)
LT (less than)
ET (equal to)

CONSTRAINTS:

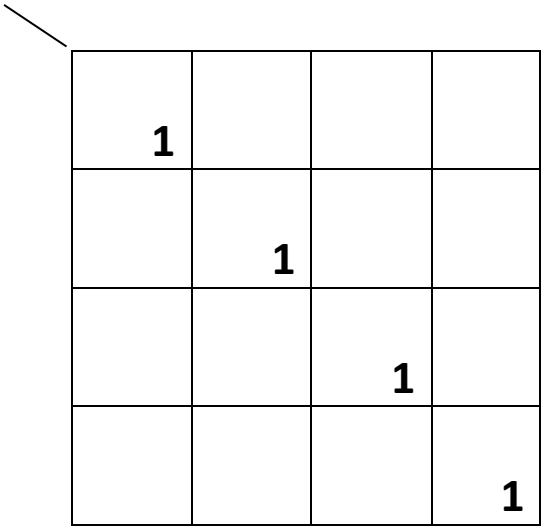
- The Boolean expressions for each output must be derived using K-maps or other methods, and simplified using algebraic rules or Boolean theorems.
- The logic circuit diagram must be drawn using the appropriate logic gates for each expression, such as AND, OR, NOT, XOR, etc.
- The functionality of the circuit must be verified by testing it with different input values and checking the outputs.

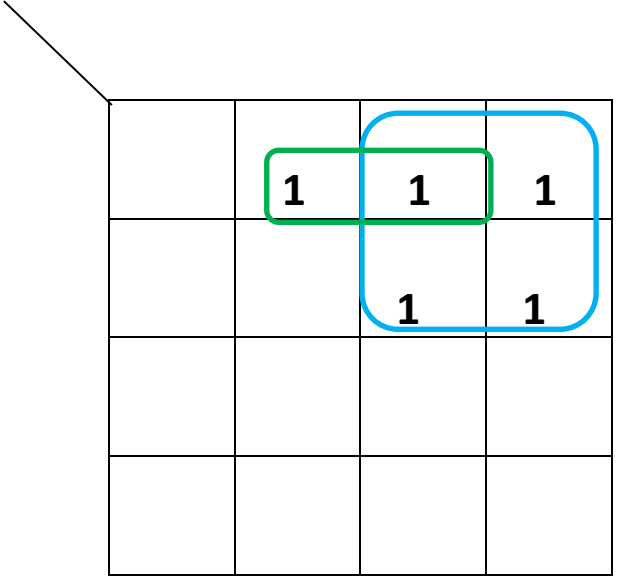
3.Methodology

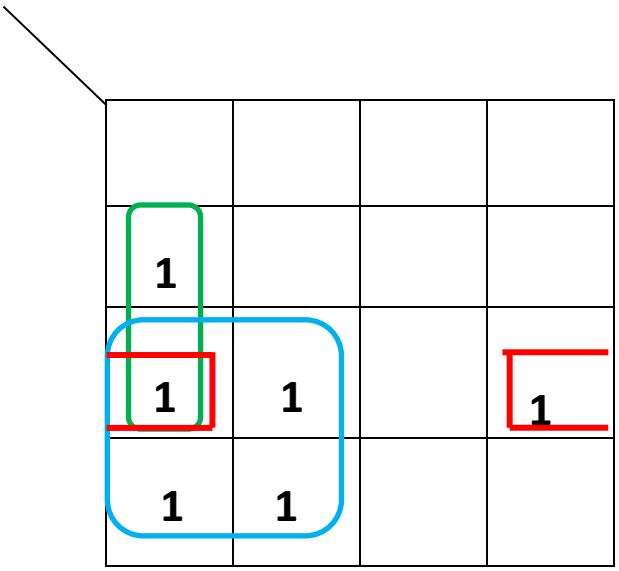
I. Generating the solution to the problem by the use of Truth table/excitation table, K- map and (or) Boolean algebra.
II. Finding out the different digital ICs to be used in the optimized design.

For 2 BIT:

A1	A0	B1	B0	ET	LT	GT
0	0	0	0	1	0	0
0	0	0	1	0	1	0
0	0	1	0	0	1	0
0	0	1	1	0	1	0
0	1	0	0	0	0	1
0	1	0	1	1	0	0
0	1	1	0	0	1	0
1	1	1	1	0	1	0
1	0	0	0	0	0	1
1	0	0	1	0	0	1
1	0	1	0	1	0	0
1	0	1	1	0	1	0
1	1	0	0	0	0	1
1	1	0	1	0	0	1
1	1	1	0	0	0	1







OBTAINED EXPRESSIONS:

FOR 2 BIT:

ET= (A0'.B0' + A0.B0) + (A1'.B1' + A1.B1)
LT=A1'.B1 + A0'.B0(A1' + B1)
GT= A1.B1' + A0.B0'(A1 + B1')

FOR 2 BIT:

S0=A0 XNOR B0
S1=A1 XNOR B1
S2=A2 XNOR B2
S3=A3 XNOR B3
ET= S3.S2.S1.S0
LT=A3'.B3 + S3.A2'.B2 + S3.S2.A1'.B1 + S3.S2.S1.A0'.B0
GT= A3.B3' + S3.A2.B2' + S3.S2.A1.B1' + S3.S2.S1.A0.B0'

DIFFERENT IC'S USED:

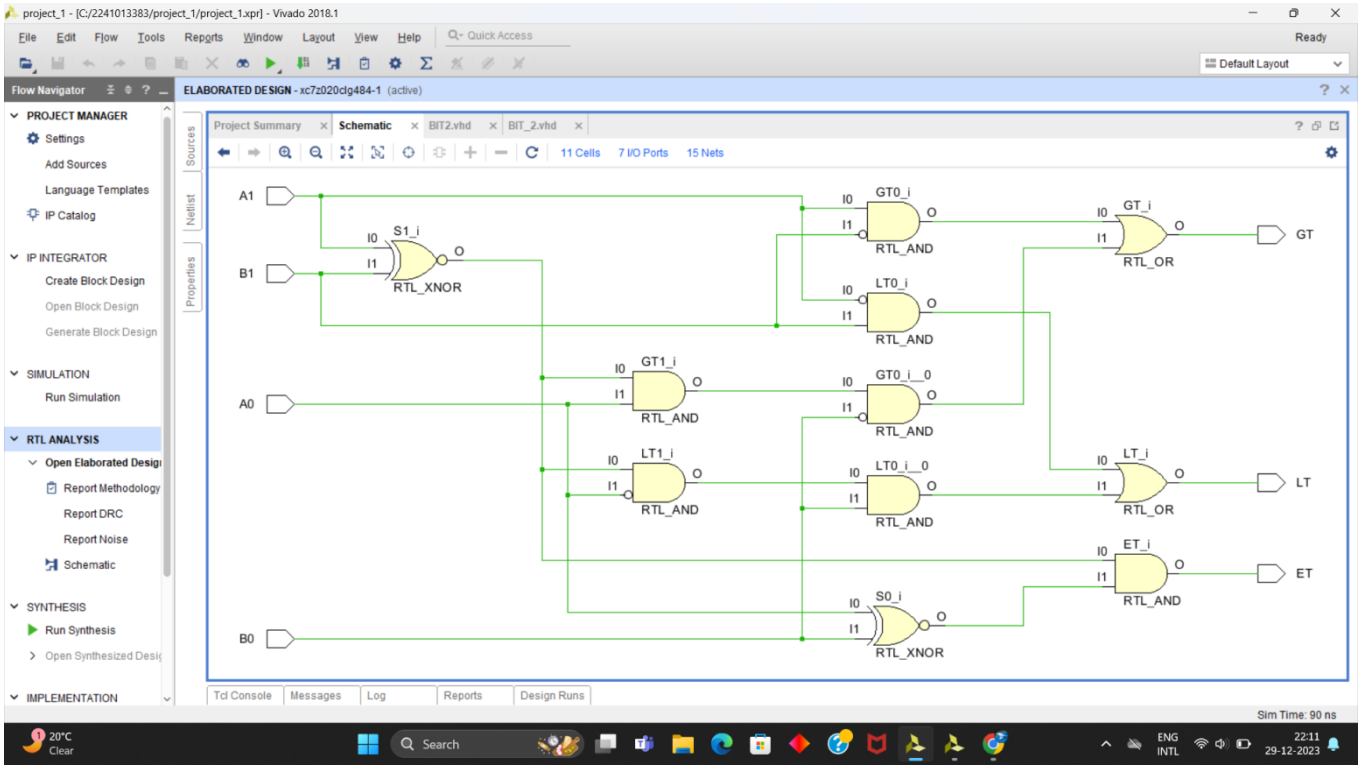
- **7432-Quad-2-input OR gate**
- **7408-Quad-2-input AND gate**
- **7486-Quad-2-input XOR gate**
- **747266-Quad-2-input XNOR gate**
- **7404-Hex Inverter-NOT gate**

4. Implementation

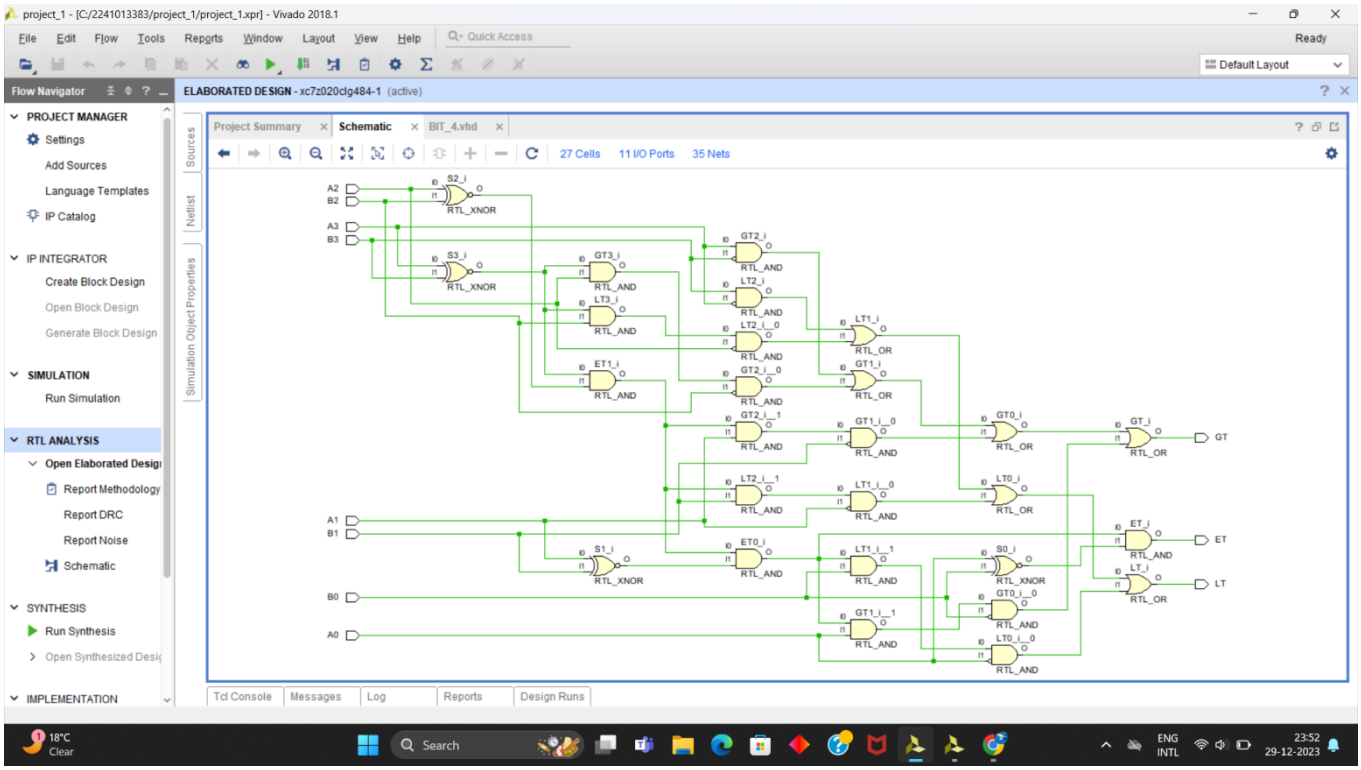
III. Drawing the logic diagram using different logic gates.

IV. Program

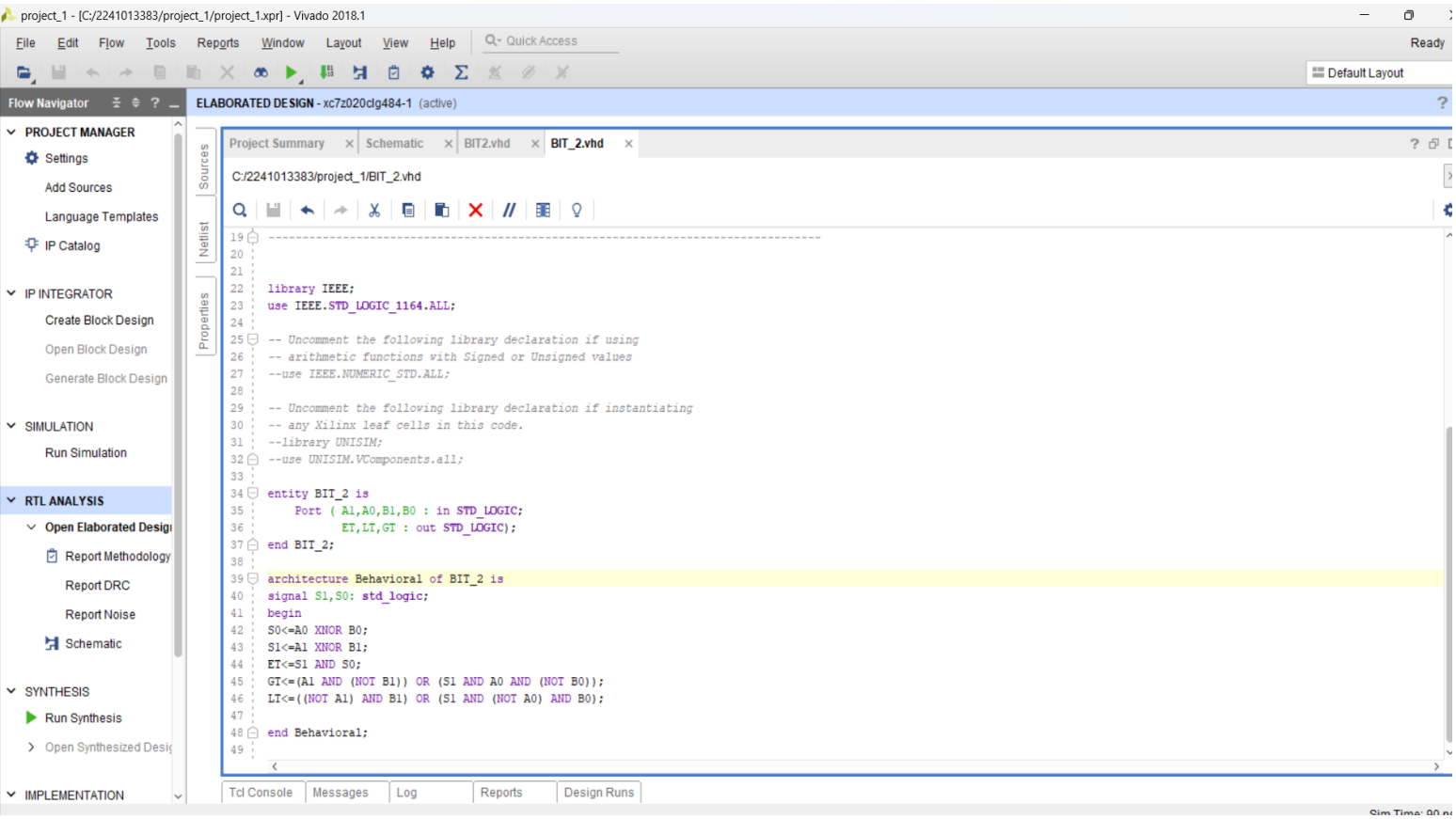
FOR 2 BIT:



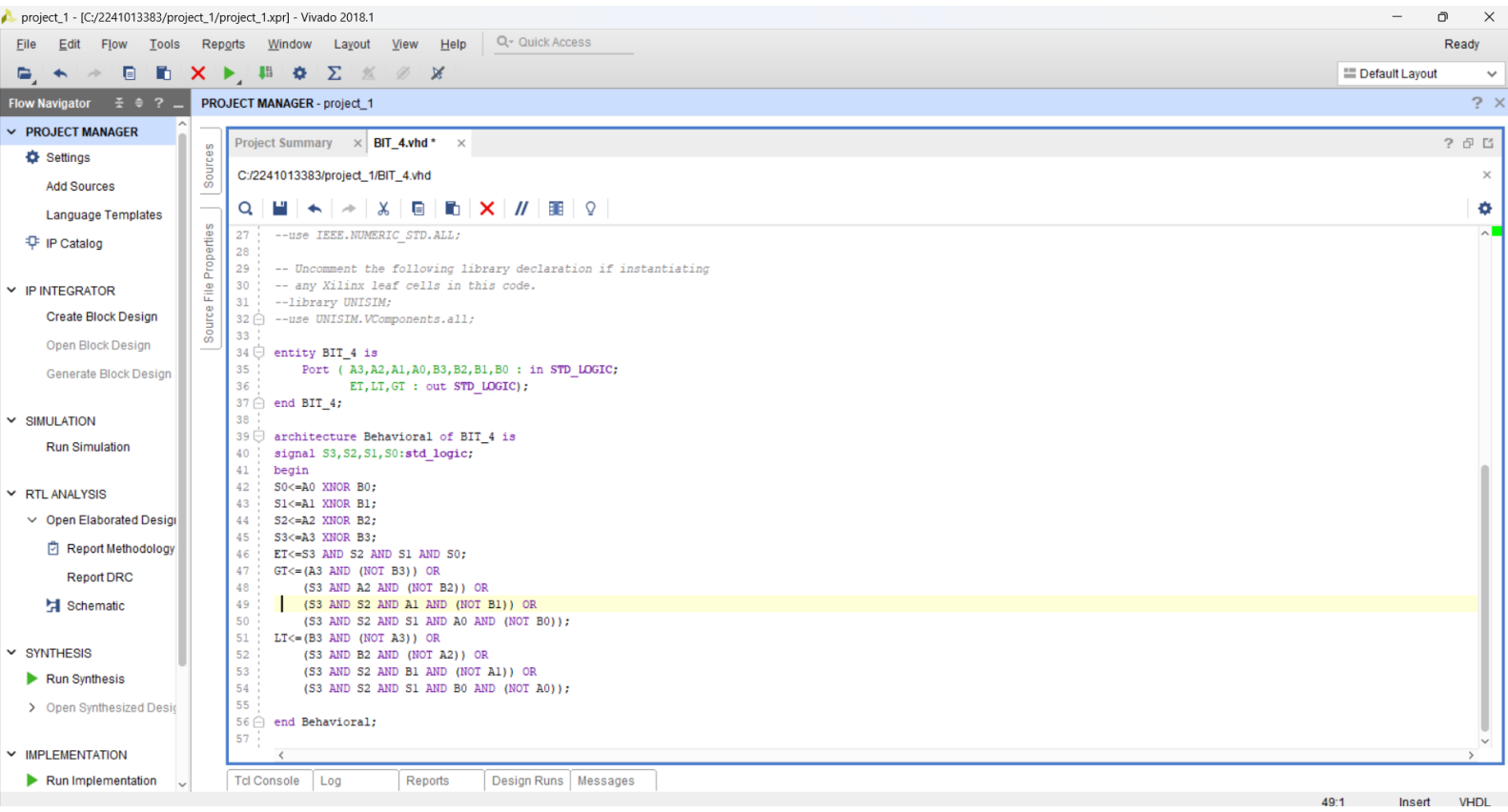
FOR 4 BIT:



PROGRAMS(FOR 2 BIT AND 4 BIT)




```
----------------------------------------------------------------------------------


library IEEE;
use IEEE.STD_LOGIC_1164.ALL;

-- Uncomment the following library declaration if using
-- arithmetic functions with Signed or Unsigned values
--use IEEE.NUMERIC_STD.ALL;

-- Uncomment the following library declaration if instantiating
-- any Xilinx leaf cells in this code.
--library UNISIM;
--use UNISIM.VComponents.all;

entity BIT_2 is
    Port ( A1,A0,B1,B0 : in STD_LOGIC;
           ET,LT,GT : out STD_LOGIC);
end BIT_2;

architecture Behavioral of BIT_2 is
signal S1,S0: std_logic;
begin
S0<=A0 XNOR B0;
S1<=A1 XNOR B1;
ET<=S1 AND S0;
GT<=(A1 AND (NOT B1)) OR (S1 AND A0 AND (NOT B0));
LT<=((NOT A1) AND B1) OR (S1 AND (NOT A0) AND B0);

end Behavioral;
```




```
--use IEEE.NUMERIC_STD.ALL;

-- Uncomment the following library declaration if instantiating
-- any Xilinx leaf cells in this code.
--library UNISIM;
--use UNISIM.VComponents.all;

entity BIT_4 is
    Port ( A3,A2,A1,A0,B3,B2,B1,B0 : in STD_LOGIC;
           ET,LT,GT : out STD_LOGIC);
end BIT_4;

architecture Behavioral of BIT_4 is
signal S3,S2,S1,S0:std_logic;
begin
S0<=A0 XNOR B0;
S1<=A1 XNOR B1;
S2<=A2 XNOR B2;
S3<=A3 XNOR B3;
ET<=S3 AND S2 AND S1 AND S0;
GT<=(A3 AND (NOT B3)) OR
    (S3 AND A2 AND (NOT B2)) OR
    (S3 AND S2 AND A1 AND (NOT B1)) OR
    (S3 AND S2 AND S1 AND A0 AND (NOT B0));
LT<=(B3 AND (NOT A3)) OR
    (S3 AND B2 AND (NOT A2)) OR
    (S3 AND S2 AND B1 AND (NOT A1)) OR
    (S3 AND S2 AND S1 AND B0 AND (NOT A0));

end Behavioral;
```

5. Results & Interpretation

Verification of the output for different inputs that satisfies the problem statement by the use of truth table.

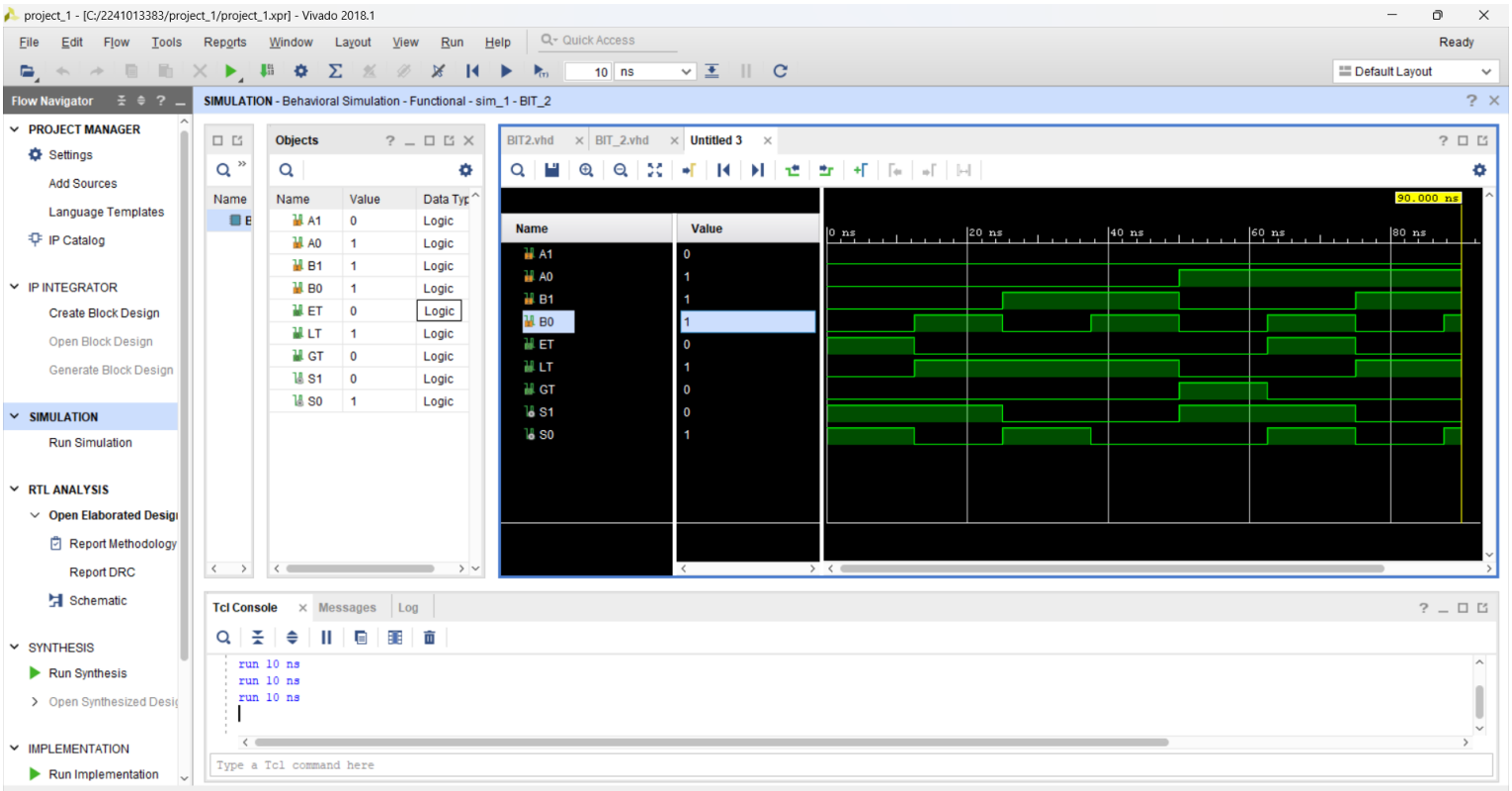
EXCPECTED OUTPUT

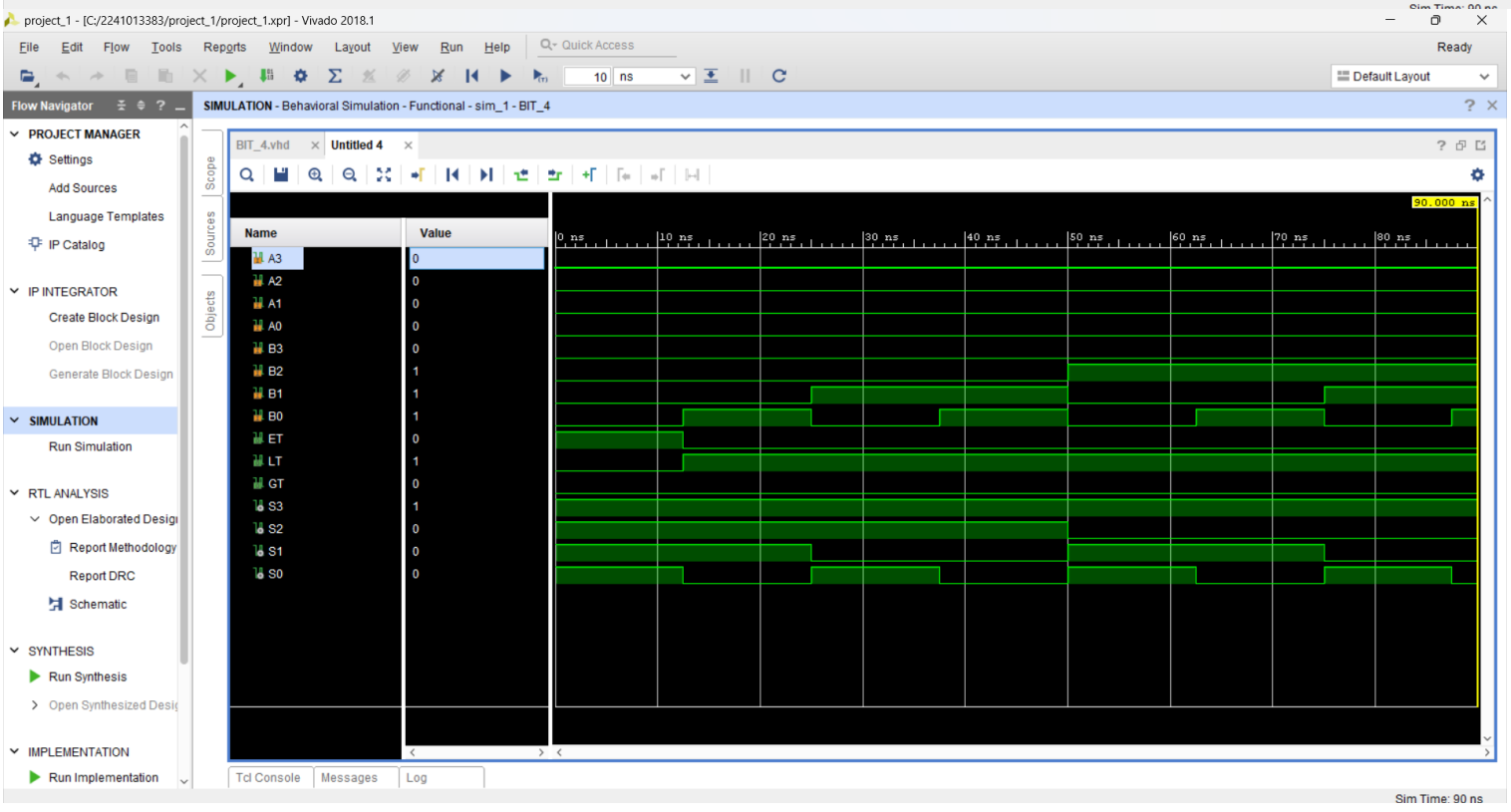
A1	A0	B1	B0	ET	LT	GT
0	0	0	0	1	0	0
0	0	0	1	0	1	0
0	0	1	0	0	1	0
0	0	1	1	0	1	0
0	1	0	0	0	0	1
0	1	0	1	1	0	0
0	1	1	0	0	1	0
1	1	1	1	0	1	0
1	0	0	0	0	0	1
1	0	0	1	0	0	1
1	0	1	0	1	0	0
1	0	1	1	0	1	0
1	1	0	0	0	0	1
1	1	0	1	0	0	1
1	1	1	0	0	0	1

OBSERVED OUTPUT

A1	A0	B1	B0	ET	LT	GT
0	0	0	0	1	0	0
0	0	0	1	0	1	0
0	0	1	0	0	1	0
0	0	1	1	0	1	0
0	1	0	0	0	0	1
0	1	0	1	1	0	0
0	1	1	0	0	1	0
1	1	1	1	0	1	0
1	0	0	0	0	0	1
1	0	0	1	0	0	1
1	0	1	0	1	0	0
1	0	1	1	0	1	0
1	1	0	0	0	0	1

1	1	0	1	0	0	1
1	1	1	0	0	0	1





6. REFERENCES:

- **Brown, L., & Miller, C. (2019). "Fundamentals of Digital Electronics: Design, Implementation, and Applications."**

- **Chang, S., & Patel, R. (2021). "Advanced Digital Circuit Design: Techniques and Applications."**

Conclusion:

We are able to design a 2 bit and 4 bit magnitude comparator and are able to successfully run it over Vivado .We verified our expected output that we had depicted from truth table and compared it with our observed output that we observed from waveform.

APPENDICES:

74LVC08A

Quad 2-input AND gate

Rev. 7 — 19 April 2016 Product data sheet

1. General description

The 74LVC08A provides four 2-input AND gates.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

2. Features and benefits

- 5 V tolerant inputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Complies with JEDEC standard:
  - JESD8-7A (1.65 V to 1.95 V)
  - JESD8-5A (2.3 V to 2.7 V)
  - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-B exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC08AD	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LVC08ADB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LVC08APW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LVC08ABQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

4. Functional diagram

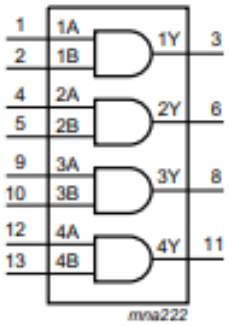


Fig 1. Logic symbol

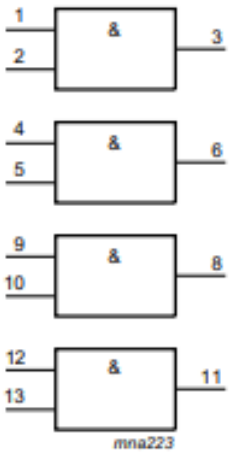


Fig 2. IEC logic symbol

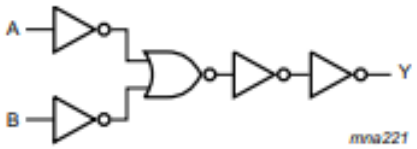


Fig 3. Logic diagram for one gate

5. Pinning information

5.1 Pinning

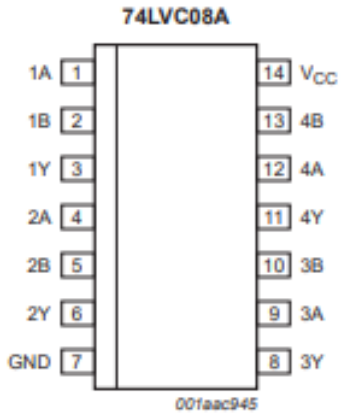
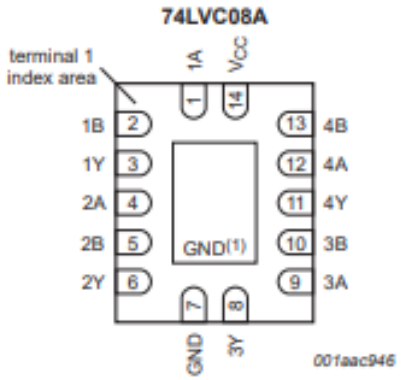


Fig 4. Pin configuration SO14 and (T)SSOP14



Transparent top view

(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN14

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V_{CC}	14	supply voltage

6. Functional description

Table 3. Function selection[1]

Input		Output
nA	**nB**	**nY**
L	X	L
X	L	L
H	H	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		−50	-	mA
V_I	input voltage		[1]	−0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		-	±50	mA
V_O	output voltage	output HIGH or LOW-state	[2]	−0.5	V_{CC} + 0.5	V
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			−100	-	mA
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[3]	-	500	mW
T_{stg}	storage temperature			−65	+150	°C

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SO14 packages: above 70 °C derate linearly with 8 mW/K.
For (T)SSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.
For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	output HIGH or LOW-state	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
		V_{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	0.65 × V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = −100 µA; V_{CC} = 1.65 V to 3.6 V	V_{CC} − 0.2	-	-	V_{CC} − 0.3	-	V
		I_O = −4 mA; V_{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I_O = −8 mA; V_{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I_O = −12 mA; V_{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I_O = −18 mA; V_{CC} = 3.0 V	2.4	-	-	2.25	-	V
		I_O = −24 mA; V_{CC} = 3.0 V	2.2	-	-	2.0	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100 µA; V_{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	0.6	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	-	0.8	V
I_I	input leakage current	V_{CC} = 3.6 V; V_I = 5.5 V or GND	-	±0.1	±5	-	±20	µA

Table 6. Static characteristics *...continued*

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
I_{CC}	supply current	V_{CC} = 3.6 V; V_I = V_{CC} or GND; I_O = 0 A	-	0.1	10	-	40	µA
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 2.7 V to 3.6 V; V_I = V_{CC} – 0.6 V; I_O = 0 A	-	5	500	-	5000	µA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND to V_{CC}	-	4.0	-	-	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, nB to nY; see Figure 6 [2]						
		V_{CC} = 1.2 V	-	11.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	0.5	4.2	9.0	0.5	10.4	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.5	6.9	1.0	8.0	ns
		V_{CC} = 2.7 V	1.5	2.5	4.8	1.5	5.6	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.3	4.1	1.0	4.8	ns
$t_{sk(o)}$	output skew time	V_{CC} = 3.0 V to 3.6 V [3]	-	-	1.0	-	1.5	ns
C_{PD}	power dissipation capacitance	per gate; V_I = GND to V_{CC} [4]						
		V_{CC} = 1.65 V to 1.95 V	-	4.4	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	7.7	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V	-	10.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz, f_o = output frequency in MHz

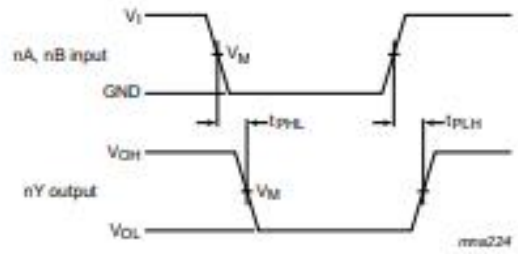
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. AC waveforms

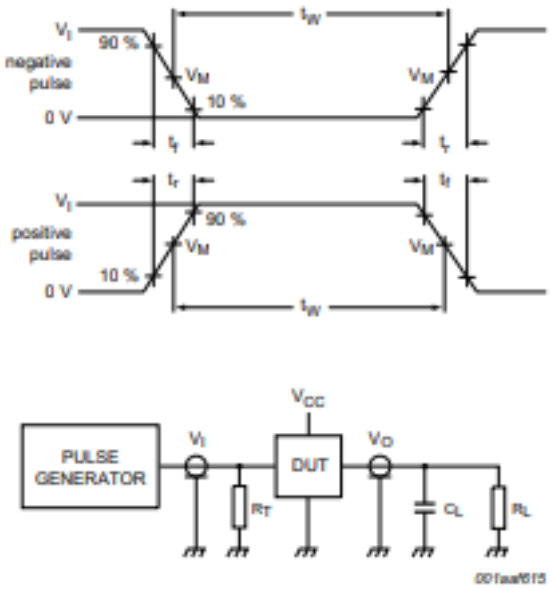


$V_M = 1.5$ V at $V_{CC} \geq 2.7$ V

$V_M = 0.5 \times V_{CC}$ at $V_{CC} < 2.7$ V

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The input nA, nB to output nY propagation delays



Test data is given in Table 8. Definitions for test circuit:

R_L = Load resistance

C_L = Load capacitance including jig and probe capacitance

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

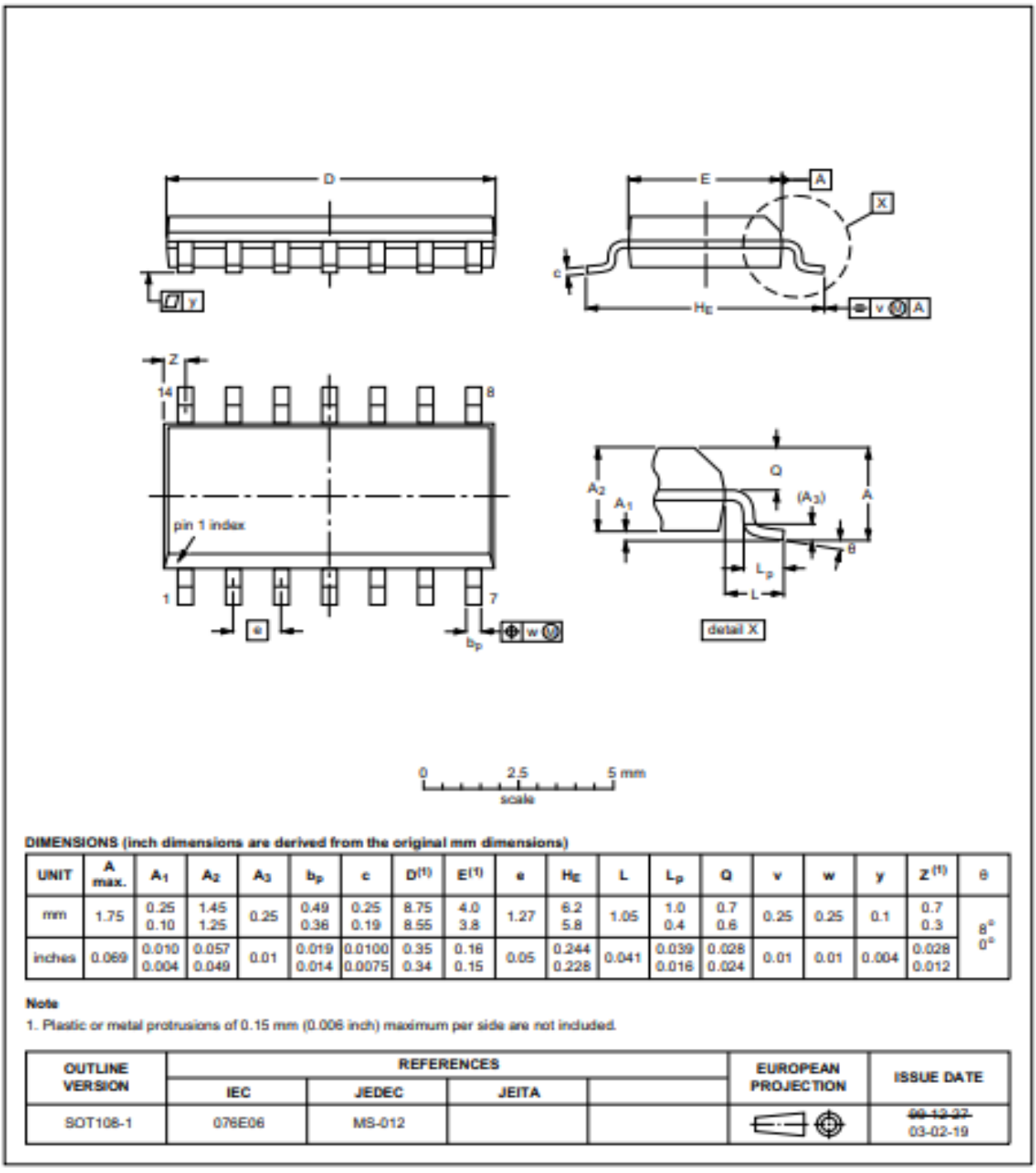
Fig 7. Test circuit for measuring switching times

Table 8. Test data

Supply voltage	Input		Load	
	V_I	t_r, t_f	C_L	R_L
1.2 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ
1.65 V to 1.95 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ
2.3 V to 2.7 V	V_{CC}	≤ 2 ns	30 pF	500 Ω
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

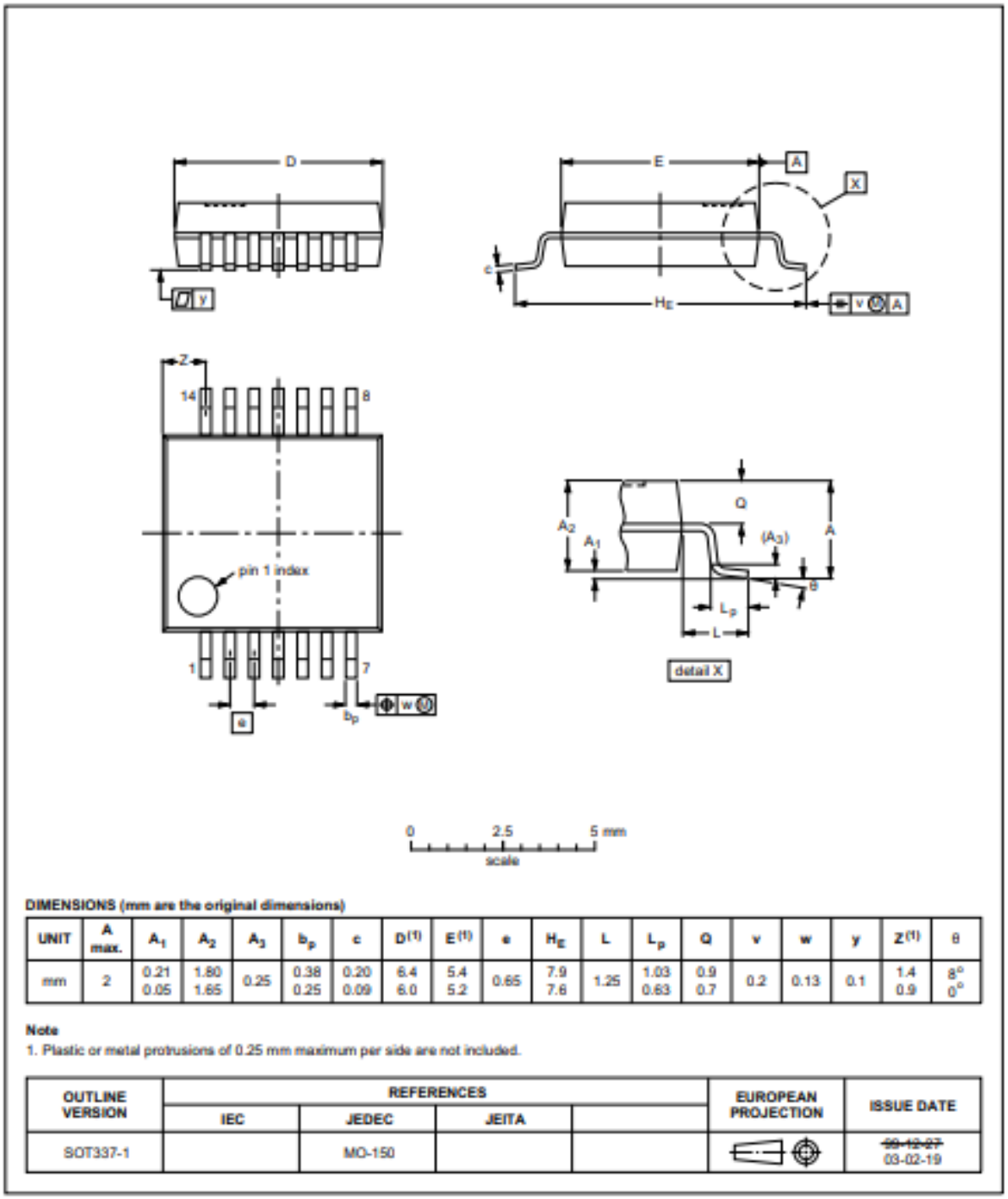
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 8. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm **SOT337-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	H_E	L	L_p	Q	v	w	y	Z(1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

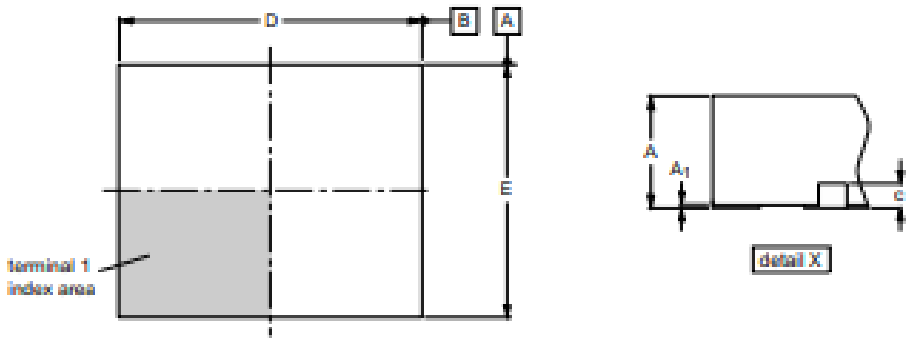
Note

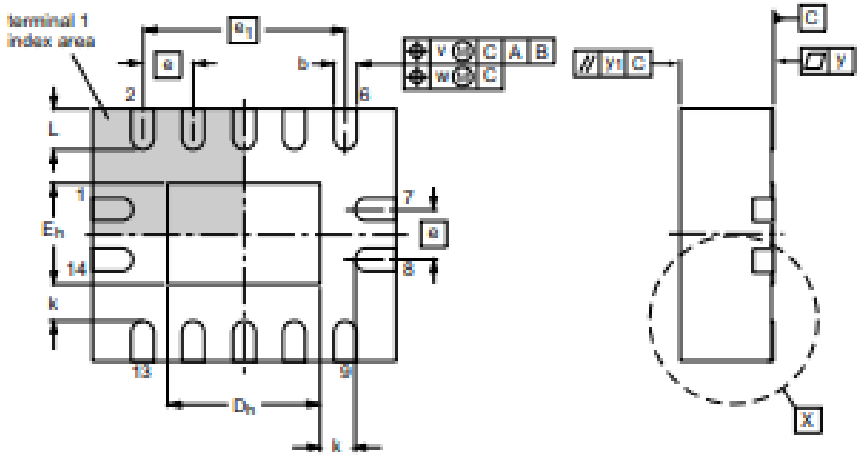
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT337-1		MO-150				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT337-1 (SSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm **SOT762-1**





Dimensions (mm are the original dimensions)

Unit		A(1)	A1	b	c	D(1)	Dh	E(1)	Eh	e	e1	k	L	v	w	y	y1
	max	1	0.05	0.30		3.1	1.65	2.6	1.15				0.5				
mm	nom		0.02	0.25	0.2	3.0	1.50	2.5	1.00	0.5	2		0.4	0.1	0.05	0.05	0.1
	min		0.00	0.18		2.9	1.35	2.4	0.85			0.2	0.3				

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot762-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT762-1		MO-241				~~15-04-10~~ 15-05-05

Fig 11. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC08A v.7	20160419	Product data sheet		74LVC08A v.6
Modifications:	• Table 2: Pin description for 1A to 4A inputs and 1Y to 4Y outputs swapped (errata).			
74LVC08A v.6	20111216	Product data sheet		74LVC08A v.5
Modifications:	• The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 4, Table 5, Table 6, Table 7 and Table 8: values added for lower voltage ranges.			
74LVC08A v.5	20030224	Product specification	-	74LVC08A v.4
74LVC08A v.4	20021030	Product specification	-	74LVC08A v.3
74LVC08A v.3	20020308	Product specification	-	74LVC08A v.2
74LVC08A v.2	19970630	Product specification	-	74LVC08A v.1
74LVC08A v.1	19970630	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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FAIRCHILD SEMICONDUCTOR™

June 1986
Revised March 2000

DM74LS32
Quad 2-Input OR Gate

General Description

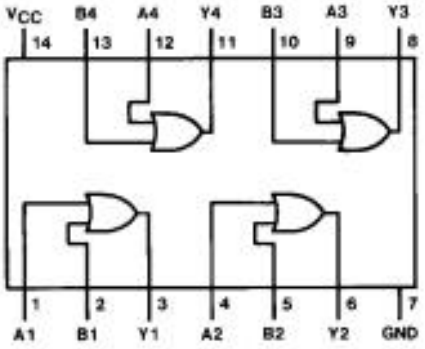
This device contains four independent gates each of which performs the logic OR function.

Ordering Code:

Order Number	Package Number	Package Description
DM74LS32M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
DM74LS32SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
DM74LS32N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram



Function Table

$Y = A + B$

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

H = HIGH Logic Level
L = LOW Logic Level

Absolute Maximum Ratings(Note 1)

Supply Voltage	7V
Input Voltage	7V
Operating Free Air Temperature Range	0°C to +70°C
Storage Temperature Range	−65°C to +150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Recommended Operating Conditions

Symbol	Parameter	Min	Nom	Max	Units
V_{CC}	Supply Voltage	4.75	5	5.25	V
V_{IH}	HIGH Level Input Voltage	2			V
V_{IL}	LOW Level Input Voltage			0.8	V
I_{OH}	HIGH Level Output Current			−0.4	mA
I_{OL}	LOW Level Output Current			8	mA
T_A	Free Air Operating Temperature	0		70	°C

Electrical Characteristics

over recommended operating free air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
V_I	Input Clamp Voltage	V_{CC} = Min, I_I = −18 mA			−1.5	V
V_{OH}	HIGH Level Output Voltage	V_{CC} = Min, I_{OH} = Max, V_{IH} = Min	2.7	3.4		V
V_{OL}	LOW Level Output Voltage	V_{CC} = Min, I_{OL} = Max, V_{IL} = Max		0.35	0.5	V
		I_{OL} = 4 mA, V_{CC} = Min		0.25	0.4	
I_I	Input Current @ Max Input Voltage	V_{CC} = Max, V_I = 7V			0.1	mA
I_{IH}	HIGH Level Input Current	V_{CC} = Max, V_I = 2.7V			20	µA
I_{IL}	LOW Level Input Current	V_{CC} = Max, V_I = 0.4V			−0.36	mA
I_{OS}	Short Circuit Output Current	V_{CC} = Max (Note 3)	−20		−100	mA
I_{CCH}	Supply Current with Outputs HIGH	V_{CC} = Max		3.1	6.2	mA
I_{CCL}	Supply Current with Outputs LOW	V_{CC} = Max		4.9	9.8	mA

Note 2: All typicals are at V_{CC} = 5V, T_A = 25°C.

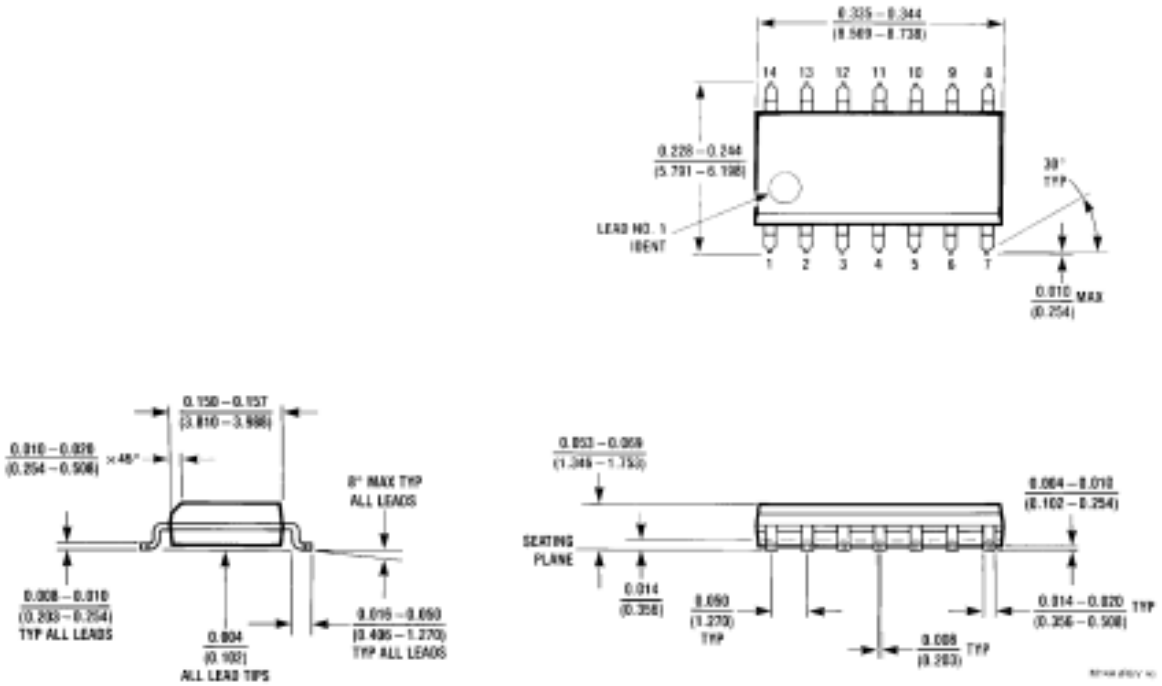
Note 3: Not more than one output should be shorted at a time, and the duration should not exceed one second.

Switching Characteristics

at V_{CC} = 5V and T_A = 25°C

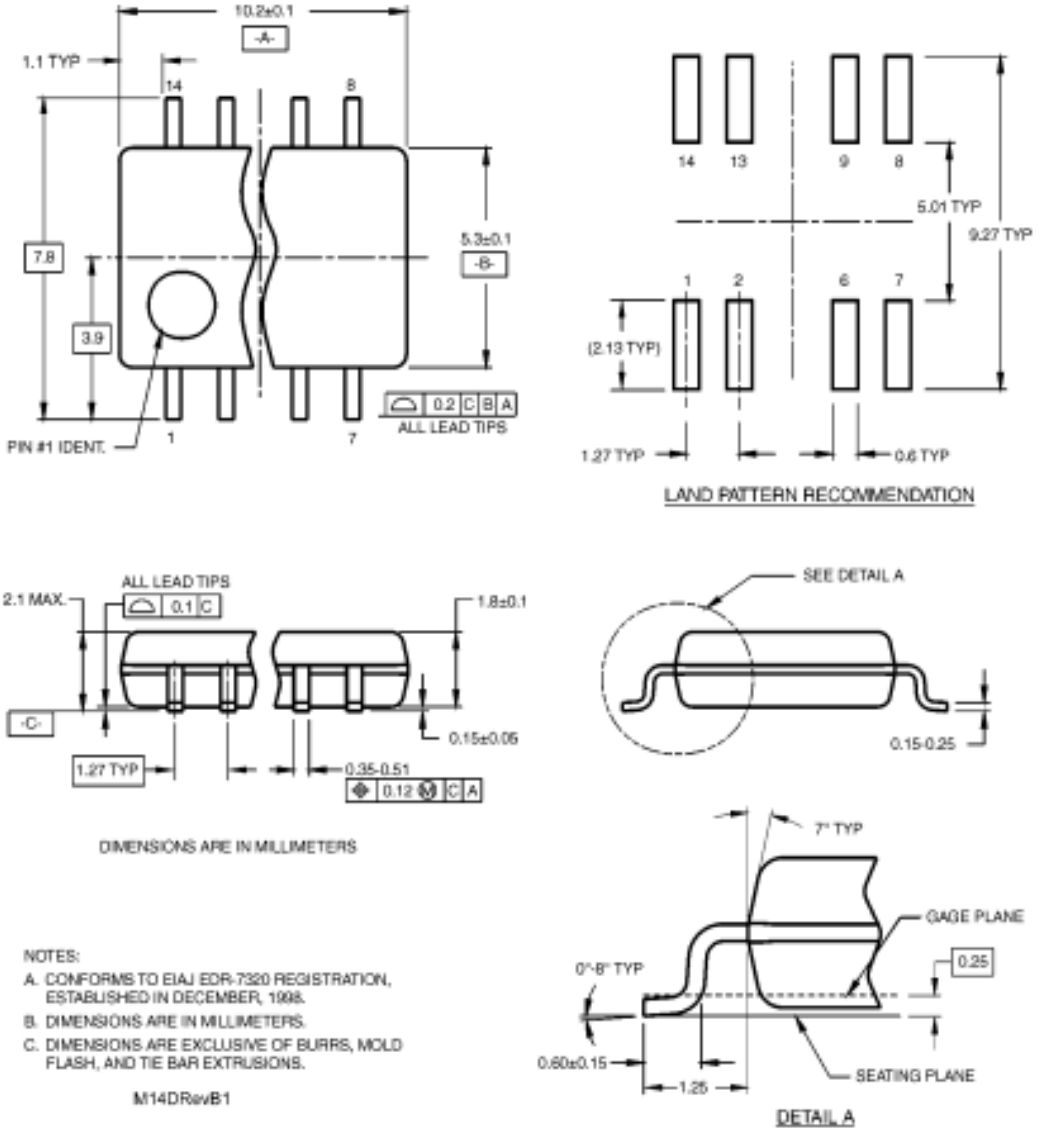
Symbol	Parameter	R_L = 2 kΩ				Units
		C_L = 15 pF		C_L = 50 pF		
		Min	Max	Min	Max	
t_{PLH}	Propagation Delay Time LOW-to-HIGH Level Output	3	11	4	15	ns
t_{PHL}	Propagation Delay Time HIGH-to-LOW Level Output	3	11	4	15	ns

Physical Dimensions inches (millimeters) unless otherwise noted



14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
Package Number M14A

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



NOTES:

A. CONFORMS TO EIAJ EDR-7320 REGISTRATION, ESTABLISHED IN DECEMBER, 1998.

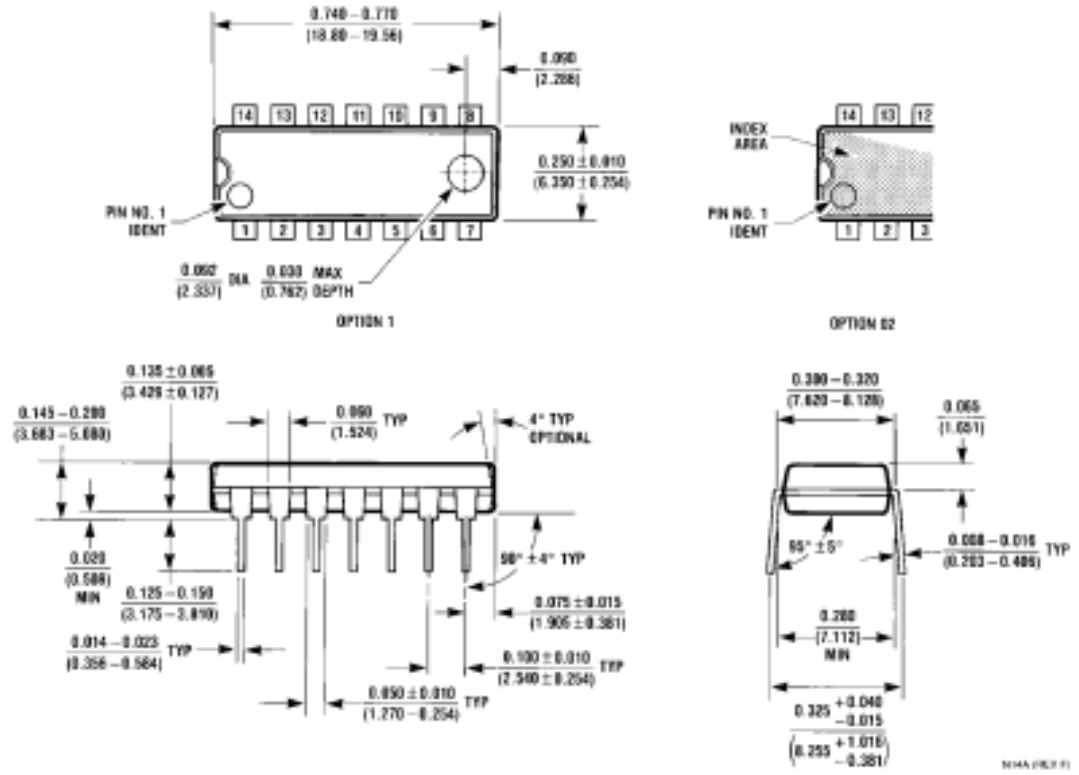
B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

M14DRevB1

14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
Package Number M14D

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide
Package Number N14A

SGS-THOMSON MICROELECTRONICS

M54HC04
M74HC04

HEX INVERTER

- HIGH SPEED
  t_{PD} = 6 ns (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 1 µA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS04

B1R
(Plastic Package)

F1R
(Ceramic Package)

M1R
(Micro Package)

C1R
(Chip Carrier)

ORDER CODES :

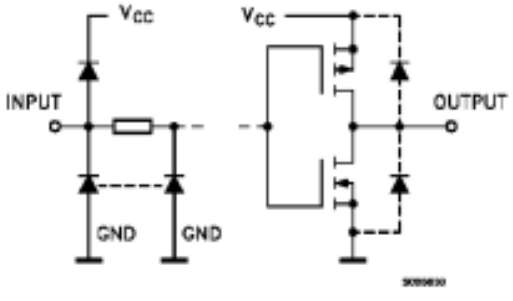
M54HC04F1R	M74HC04M1R
M74HC04B1R	M74HC04C1R

DESCRIPTION

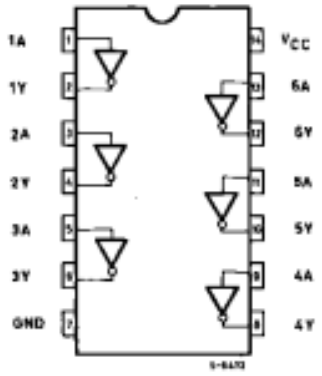
The M54/74HC04 is a high speed CMOS HEX INVERTER fabricated in silicon gate C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

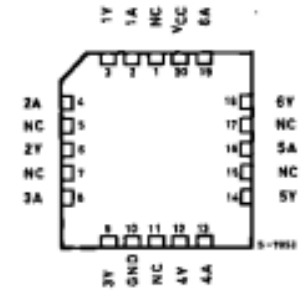
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output. All inputs are equipped with circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



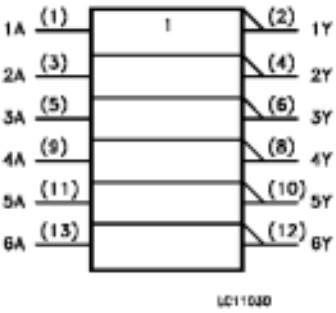


NC =
No Internal
Connection

TRUTH TABLE

A	Y
L	H
H	L

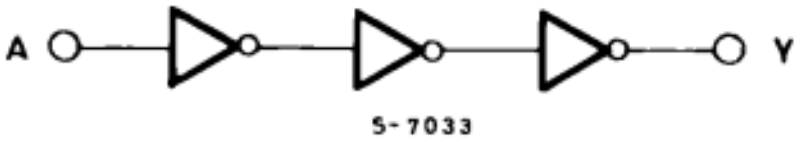
IEC LOGIC SYMBOL



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

LOGIC DIAGRAM (Per Gate)



5-7033

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: = 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	°C °C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

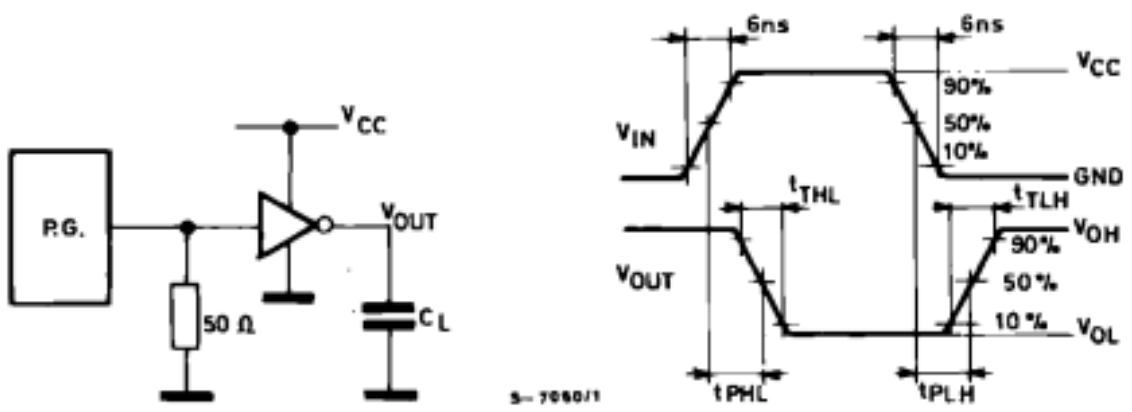
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				1		10		20	µA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

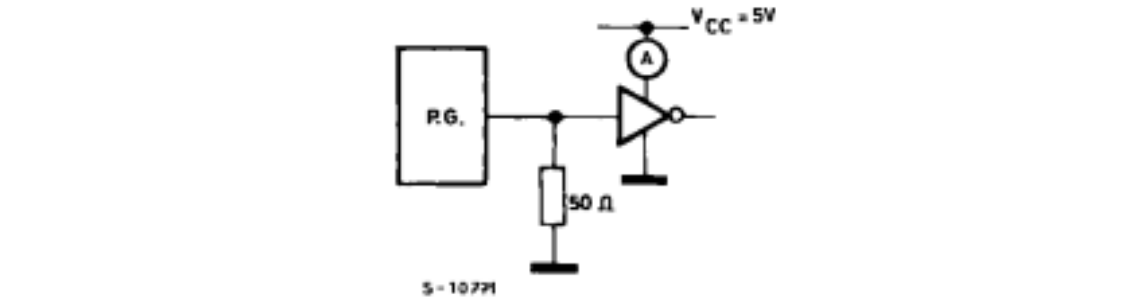
Symbol	Parameter	Test Conditions		Value							Unit
		V_{CC} (V)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0			27	75		95		110	ns
		4.5			9	15		19		22	
		6.0			8	13		16		19	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				22						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6$ (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT



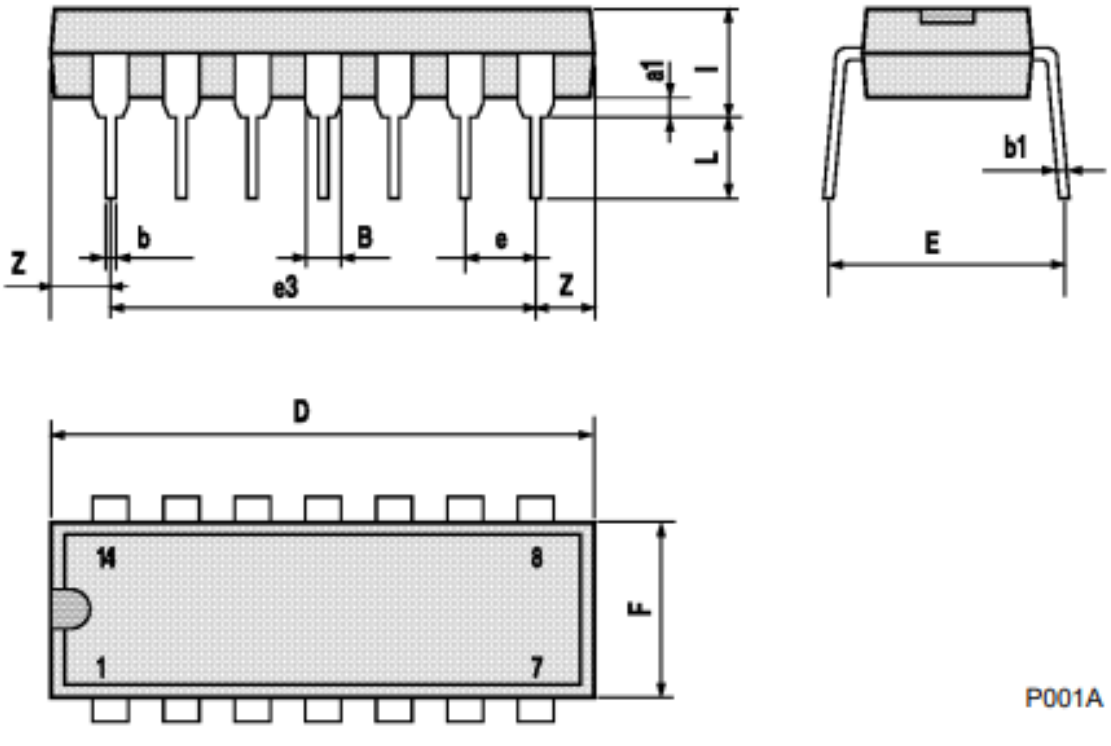
TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

Plastic DIP14 MECHANICAL DATA

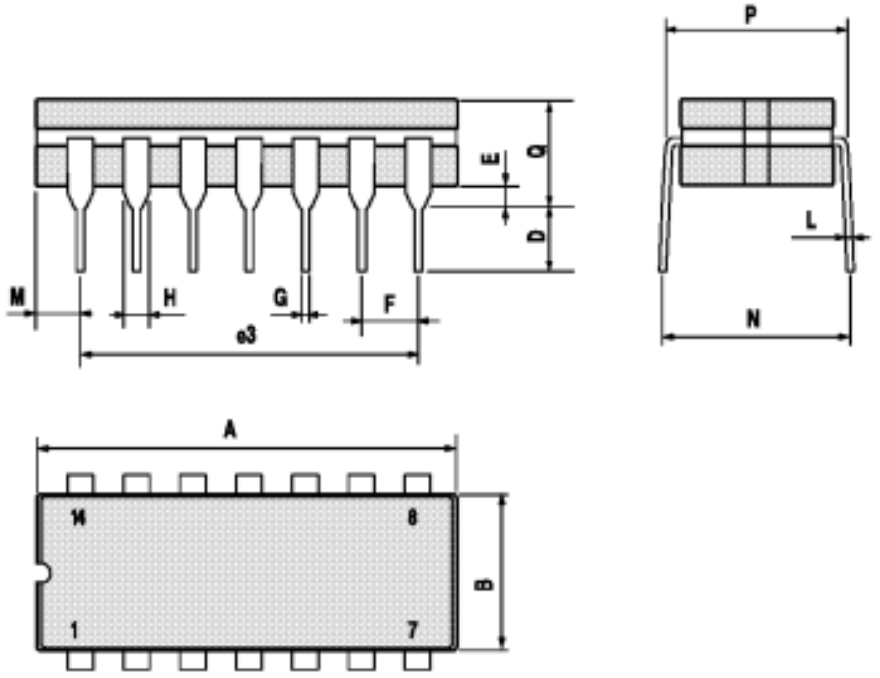
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

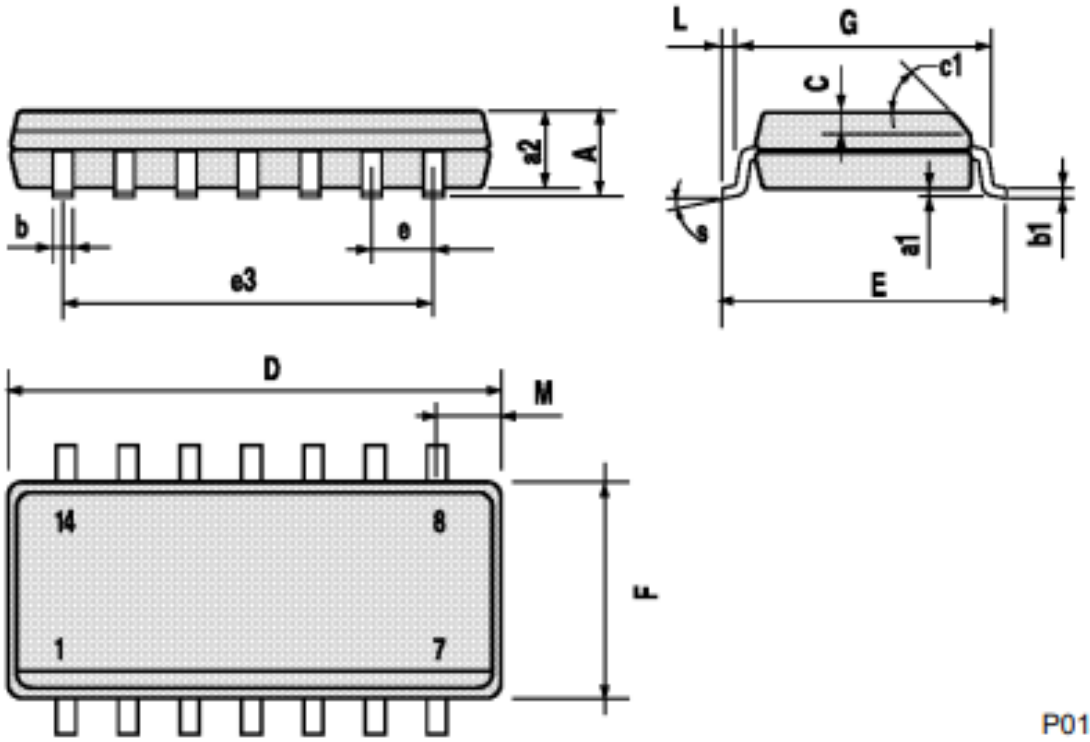
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

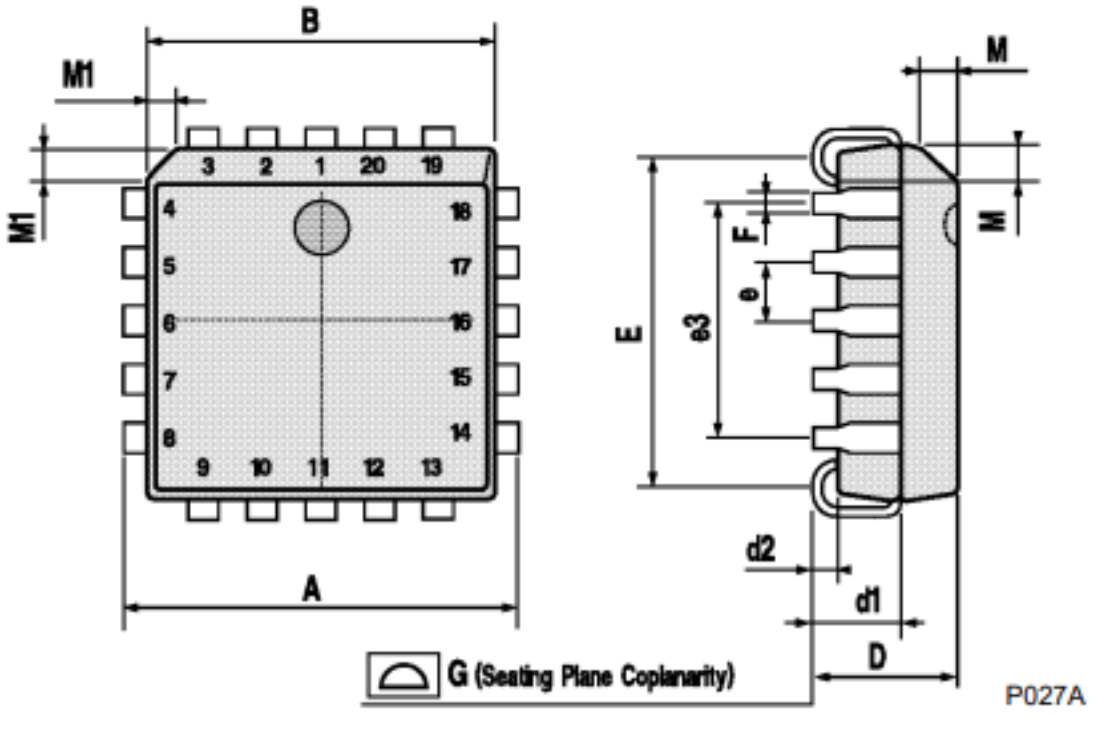
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



MC74VHC86

Quad 2-Input XOR Gate

The MC74VHC86 is an advanced high speed CMOS 2−input Exclusive−OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

Features

- High Speed: t_{PD} = 4.8 ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: I_{CC} = 2 μA (Max) at T_A = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model (HBM) > 2000 V; Machine Model > 200 V
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

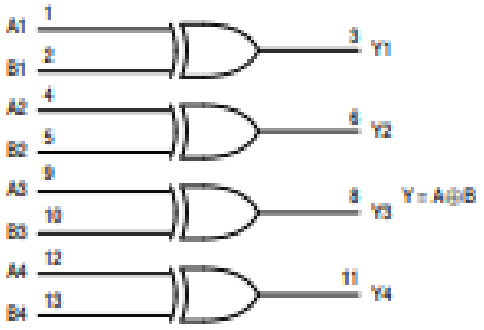


Figure 1. Logic Diagram

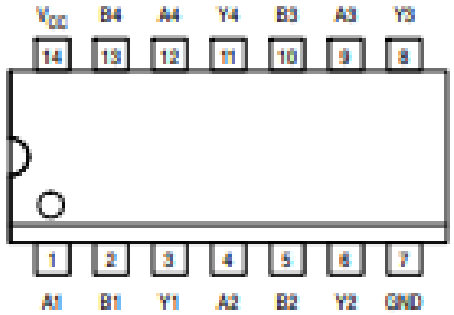


Figure 2. Pinout: 14−Lead Packages (Top View)

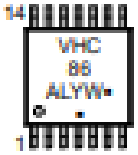
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

SOIC−14
D SUFFIX
CASE 751A

TSSOP−14
DT SUFFIX
CASE 948G



A = Assembly Location
WL, L = Wafer Lot
Y, YY = Year
WW, W = Work Week
G or • = Pb−Free Package
(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	–0.5 to +7.0	V
V_{in}	DC Input Voltage	–0.5 to +7.0	V
V_{out}	DC Output Voltage	–0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current	−20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Package†	500	mW
	TSSOP Package†	450	
T_{stg}	Storage Temperature	–65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating SOIC Package: – 7 mW/°C from 65° to 125°C
TSSOP Package: − 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{in}	DC Input Voltage		0	5.5	V
V_{out}	DC Output Voltage		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 3.3 V ±0.3 V	0	100	ns/V
		V_{CC} = 5.0 V ±0.5 V	0	20	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	T_A = 25°C			T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0 3.0 to 5.5	1.50 V_{CC} x 0.7			1.50 V_{CC} x 0.7		V
V_{IL}	Low−Level Input Voltage		2.0 3.0 to 5.5			0.50 V_{CC} x 0.3		0.50 V_{CC} x 0.3	V
V_{OH}	High−Level Output Voltage	V_{in} = V_{IH} or V_{IL} I_{OH} = −50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V_{in} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		
V_{OL}	Low−Level Output Voltage	V_{in} = V_{IH} or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5		0 0 0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44	
I_{in}	Input Leakage Current	V_{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I_{CC}	Quiescent Supply Current	V_{in} = V_{CC} or GND	5.5			2.0		20.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T_A = 25°C			T_A = −55°C to +125°C		Unit
			Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A or B to Y	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF C_L = 50 pF		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF C_L = 50 pF		4.8 6.3	6.8 8.8	1.0 1.0	8.0 10.0	
C_{in}	Input Capacitance			4	10		10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 1.)	18	pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no−load dynamic power consumption; P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50 pF, V_{CC} = 5.0 V, Measured in SOIC Package)

Symbol	Characteristic	T_A = 25°C		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC86DR2G	SOIC−14 (Pb−Free)	2500 / Tape & Reel
MC74VHC86DTG	TSSOP−14 (Pb−Free)	96 Units / Rail
MC74VHC86DTR2G	TSSOP−14 (Pb−Free)	2500 / Tape & Reel
NLVVHC86ADTR2G*	TSSOP−14 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

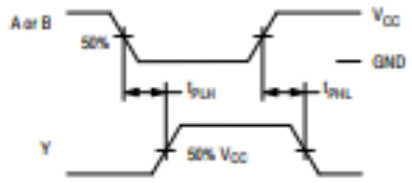
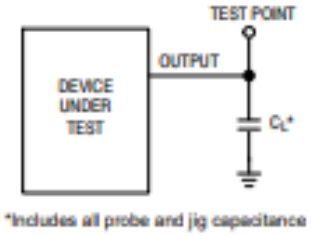


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

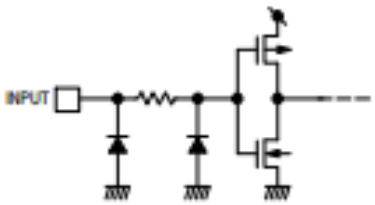


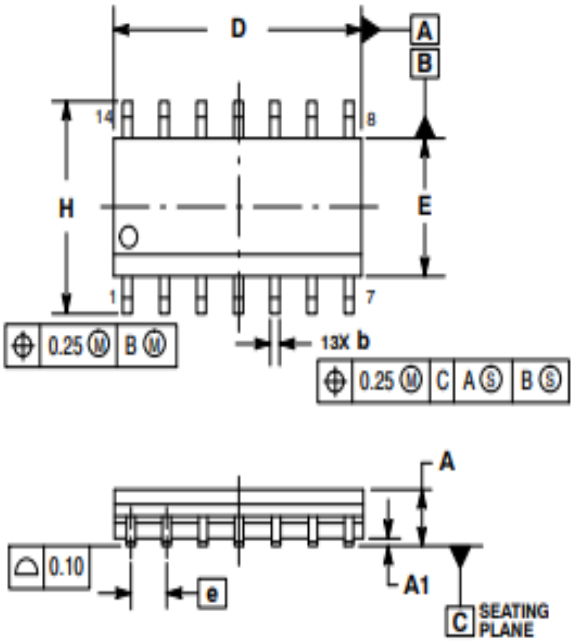
Figure 5. Input Equivalent Circuit

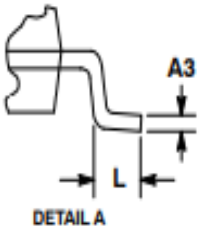
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

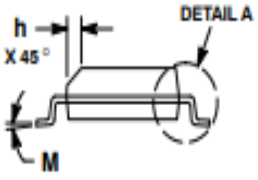
SCALE 1:1

SOIC–14 NB
CASE 751A–03
ISSUE L

DATE 03 FEB 2016



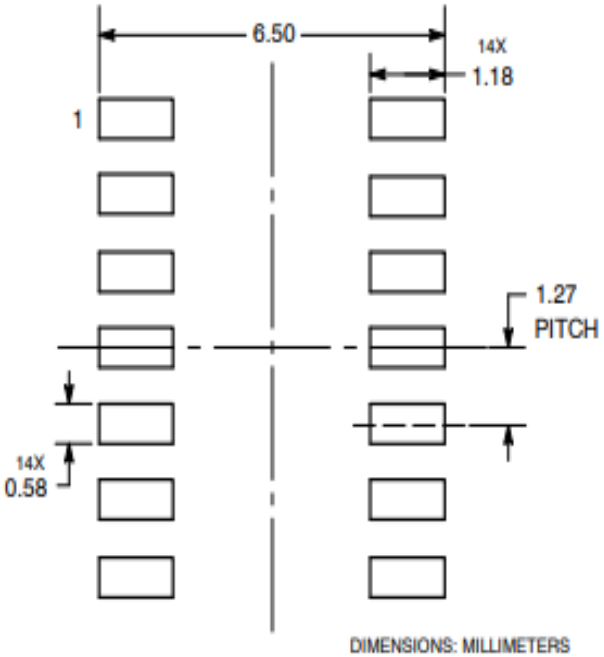




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

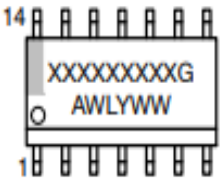
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

Product Preview

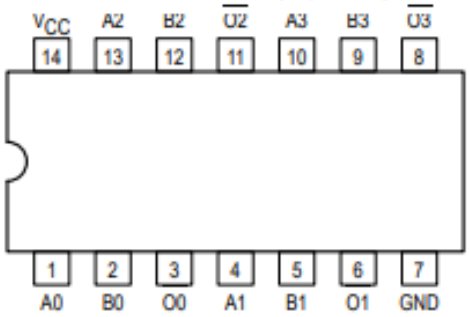
Low-Voltage CMOS Quad 2-Input XNOR Gate
With 5V-Tolerant Inputs

The MC74LCX810 is a high performance, quad 2–input XNOR gate operating from a 2.7 to 3.6V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5V allows MC74LCX810 inputs to be safely driven from 5V devices.

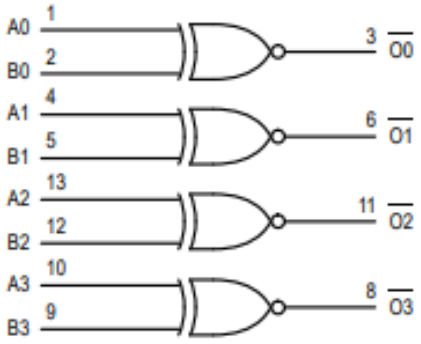
Current drive capability is 24mA at the outputs.

- Designed for 2.7 to 3.6V V_{CC} Operation
- 5V Tolerant Inputs — Interface Capability With 5V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V

Pinout: 14–Lead (Top View)



LOGIC DIAGRAM



This document contains information on a product under development. Motorola reserves the right to change or discontinue this product without notice.

MC74LCX810

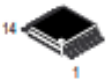
LCX

LOW–VOLTAGE CMOS QUAD 2–INPUT XNOR GATE

D SUFFIX
PLASTIC SOIC
CASE 751A–03

M SUFFIX
PLASTIC SOIC EIAJ
CASE 965–01

SD SUFFIX
PLASTIC SSOP
CASE 940A–03



DT SUFFIX
PLASTIC TSSOP
CASE 948G–01

PIN NAMES

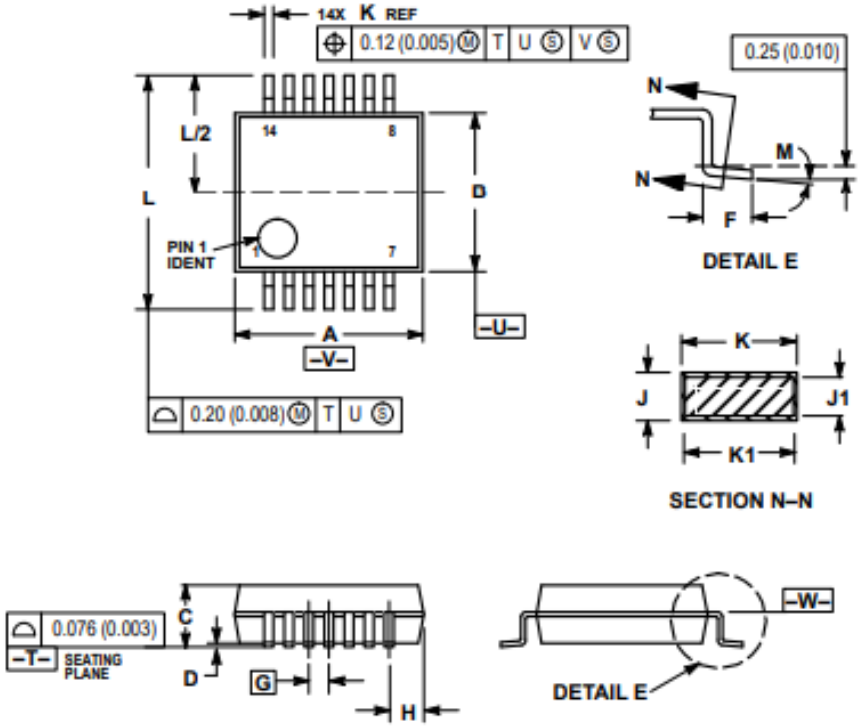
Pins	Function
An, Bn	Data Inputs
On	Outputs

FUNCTION TABLE

Inputs		Outputs
An	Bn	$\overline{On}$
L	L	H
L	H	L
H	L	L
H	H	H

OUTLINE DIMENSIONS

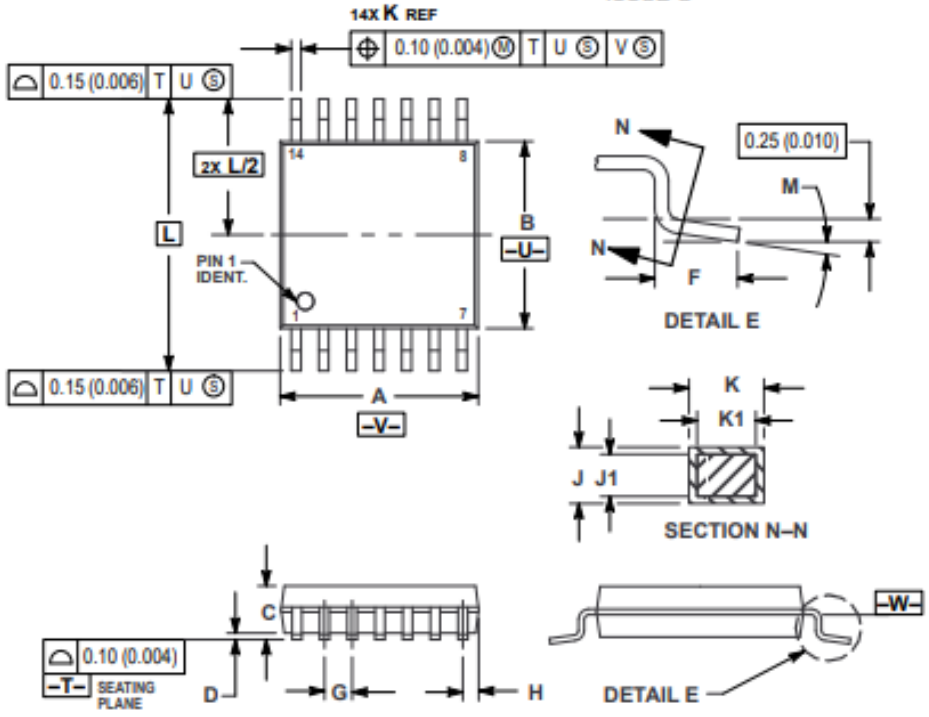
SD SUFFIX
PLASTIC SSOP PACKAGE
CASE 940A–03
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF K DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR INTRUSION SHALL NOT REDUCE DIMENSION K BY MORE THAN 0.07 (0.002) AT LEAST MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	6.07	6.33	0.238	0.249
B	5.20	5.38	0.205	0.212
C	1.73	1.99	0.068	0.078
D	0.05	0.21	0.002	0.008
F	0.63	0.95	0.024	0.037
G	0.65 BSC		0.026 BSC	
H	1.08	1.22	0.042	0.048
J	0.09	0.20	0.003	0.008
J1	0.09	0.16	0.003	0.006
K	0.25	0.38	0.010	0.015
K1	0.25	0.33	0.010	0.013
L	7.65	7.90	0.301	0.311
M	0°	8°	0°	8°

DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948G–01
ISSUE O

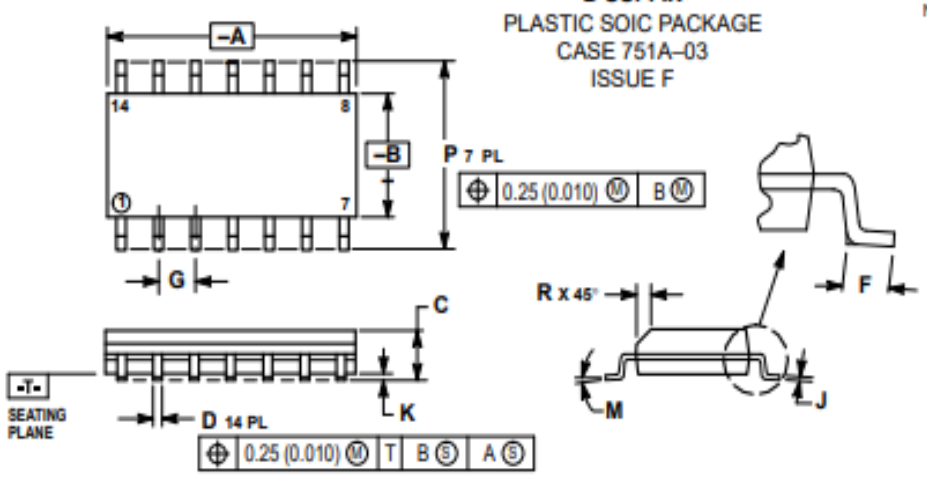


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

OUTLINE DIMENSIONS

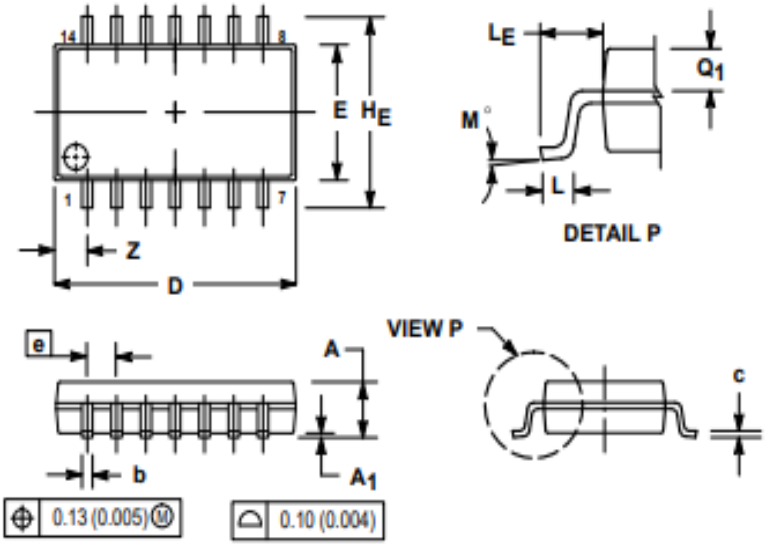
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751A–03
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

M SUFFIX
PLASTIC SOIC EIAJ PACKAGE
CASE 965–01
ISSUE O



NOTES:
1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION: MILLIMETER.
3 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	2.05	—	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q_1	0.70	0.90	0.028	0.035
Z	—	1.42	—	0.056